

DISTRIBUTED FEEDBACK LASER

GaAs Semiconductor Laser Diode
with integrated grating structure



DFB/DBR Laser

EYP-DFB-0852-00150-1500-SOT02-0000

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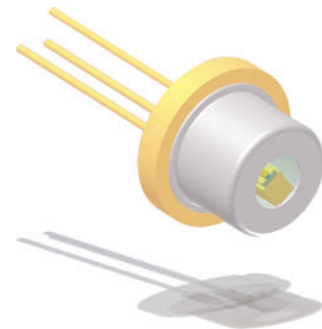
Absolute Maximum Ratings

	Symbol	Unit	min	typ	max
Operational Temperature at case	T_C	°C	–	–	50
Forward Current	I_F	mA	–	–	250
Reverse Voltage	V_R	V	–	–	0

Stress in excess of the Absolute Maximum Ratings can cause permanent damage to the device. Operation at the Absolute Maximum Rating for extended periods of time can adversely affect the device reliability and may lead to reduced operational life.

Recommended Operation Conditions

	Symbol	Unit	min	typ	max
Operational Temperature at case	T_{case}	°C	15	–	40
Forward Current	I_F	mA	–	–	230



Characteristics at $T_{amb} 25^{\circ}C$

Parameter	Symbol	Unit	min	typ	max
Center Wavelength	λ_C	nm	850	852	854
Spectral Width (FWHM)	$\Delta\nu$	MHz		2	10
Temperature Coefficient of Wavelength	$d\lambda/dT$	nm / K		0.06	
Output Power	P_{opt}	mW	100	150	
Slope Efficiency	η_d	W / A	0.6	0.8	1
Threshold Current	I_{th}	mA	60	70	90
Operational Current @ 150 mW	I_{op}	mA		230	250
Cavity Length	L	μm		1500	
Divergence parallel (FWHM)	$\Theta_{ }$	°	6	8	10
Divergence perpendicular (FWHM)	Θ_{\perp}	°	18	21	24
Polarization				TE	
Spatial Mode (transversal)				TEM ₀₀	
Spectral Mode (longitudinal)				Single Mode	

Measurement Condition / Comments

compare images on page 3
measured in homodyn-detected interferometric setup

Polarization in parallel plane
Fundamental Mode

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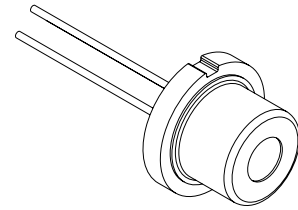
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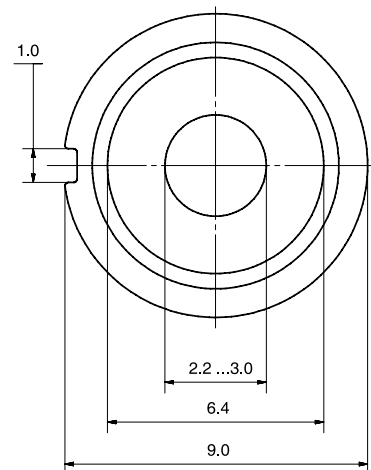
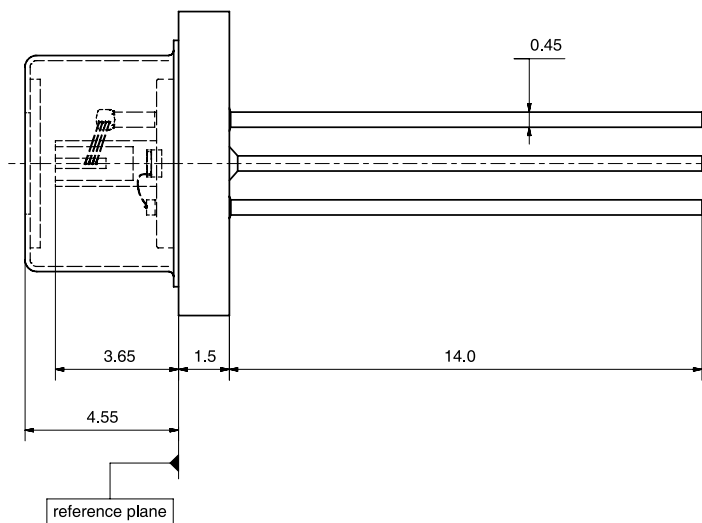
Package Information

	Part No.	
sealed SOT housing with Photodiode	SOT02	available (see image)
others		on request

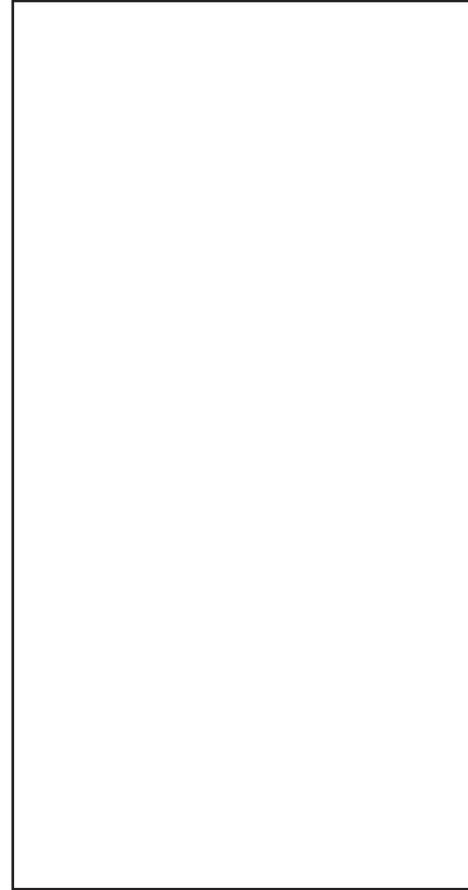
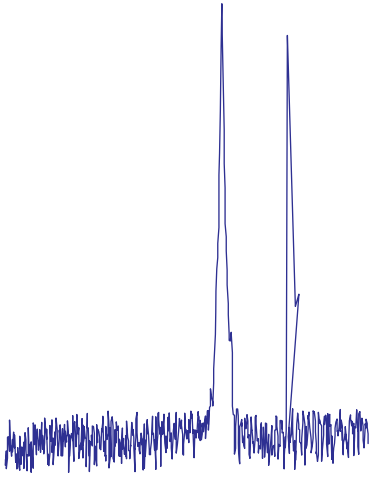


Package Dimensions

Emission plane	mm	3.65
Housing Dimension	mm	9



NARROW BANDWIDTHS



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Unpackaging, Installation and Laser Safety



Each laser diode will come with an individual data sheet verifying the parameters given within this specification.

Unpacking the laser diodes should only be done at electrostatic safe workstations (EPA). Though protection against electrostatic discharge (ESD) is implemented in the laser package, charges may occur at surfaces. Please store this product in its original package at a dry, clean place until final use. During device installation, ESD protection has to be maintained.



The DFB diode type is known to be sensitive versus optical feedback, so an optical isolator may be recommendable in some cases. Operating at moderate temperatures on proper heat sinks will contribute to a long lifetime of the diode.

The laser emission from this diode is close to the invisible infrared region of the electromagnetic spectrum. Avoid direct and/or indirect exposure to the free running beam. Collimating the free running beam with optics as common in optical instruments will increase threat to the human eye.

